

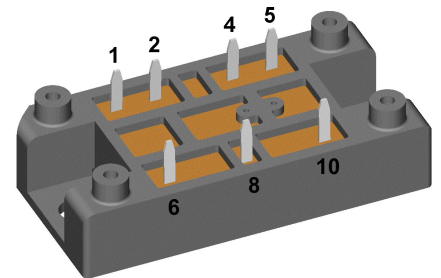
# Standard Rectifier Module

<b>3~ Rectifier</b>	
$V_{RRM} =$	1600
$I_{DAV} =$	60
$I_{FSM} =$	350

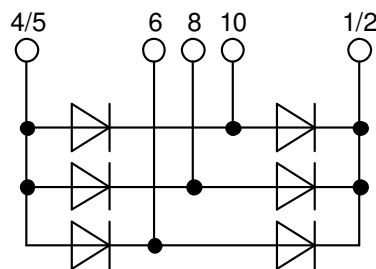
## 3~ Rectifier Bridge

**Part number**

**VUO52-16NO1**



Backside: isolated



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

### Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Package: V1-A-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

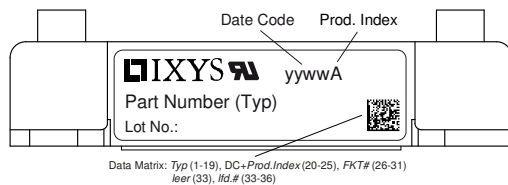
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1600	V
$I_R$	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		40	$\mu\text{A}$
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		1,5	mA
$V_F$	forward voltage drop	$I_F = 20$ A		$T_{VJ} = 25^\circ\text{C}$		1,13	V
		$I_F = 60$ A				1,44	V
		$I_F = 20$ A		$T_{VJ} = 125^\circ\text{C}$		1,07	V
		$I_F = 60$ A				1,50	V
$I_{DAV}$	bridge output current	$T_C = 110^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		60	A
		rectangular	$d = \frac{1}{3}$				
$V_{FO}$	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0,83	V
$r_F$	slope resistance					11,5	m $\Omega$
						} for power loss calculation only	
$R_{thJC}$	thermal resistance junction to case					1,3	K/W
$R_{thCH}$	thermal resistance case to heatsink				0,3		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		95	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		350	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		380	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		300	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		320	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		615	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		600	A <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		450	A <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		425	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		10	pF

Package V1-A-Pack				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>					37	g
$M_D$	mounting torque		2		2,5	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6,0			mm
$d_{Spb/Apb}$		terminal to backside	12,0			mm
$V_{ISOL}$	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



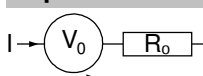
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO52-16NO1	VUO52-16NO1	Blister	24	461180

Similar Part	Package	Voltage class
VUO52-08NO1	V1-A-Pack	800
VUO52-12NO1	V1-A-Pack	1200
VUO52-14NO1	V1-A-Pack	1400
VUO52-18NO1	V1-A-Pack	1800
VUO52-20NO1	V1-A-Pack	2000
VUO52-22NO1	V1-A-Pack	2200
VUO34-16NO1	V1-A-Pack	1600
VUO34-18NO1	V1-A-Pack	1800

### Equivalent Circuits for Simulation

\* on die level

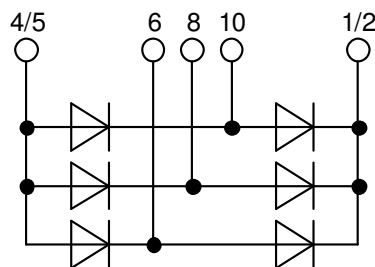
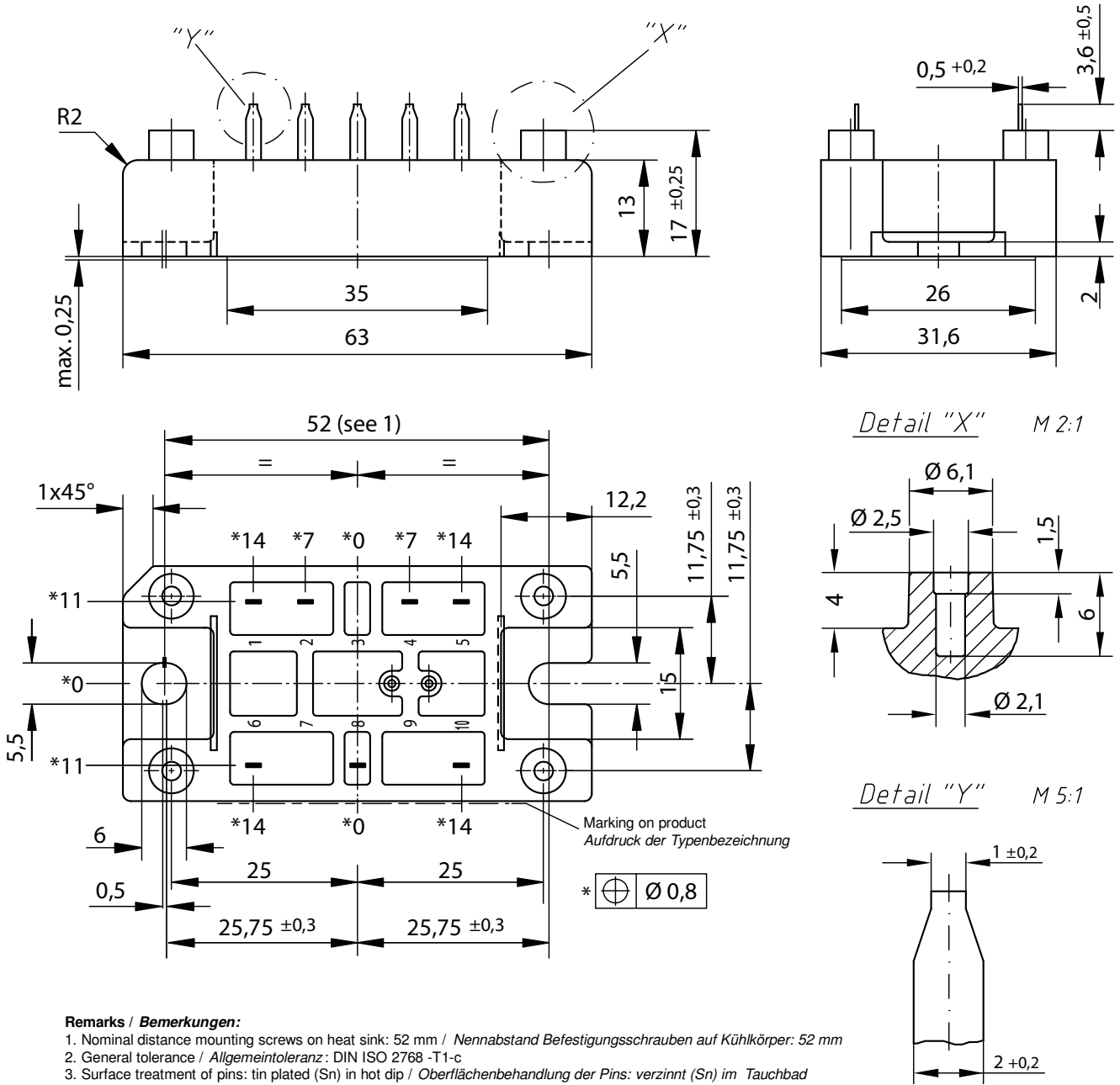
$T_{VJ} = 150\text{ °C}$



Rectifier

$V_{0\ max}$	threshold voltage	0,83	V
$R_{0\ max}$	slope resistance *	10,2	mΩ

## Outlines V1-A-Pack



## Rectifier

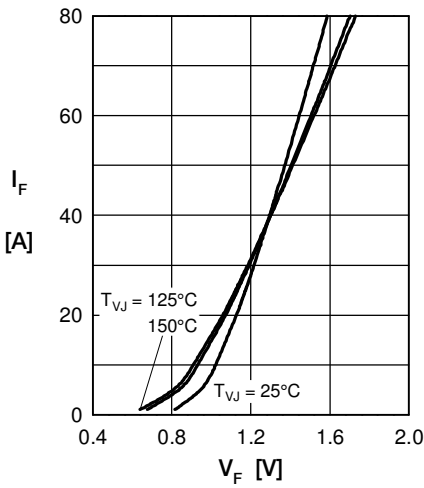


Fig. 1 Forward current vs. voltage drop per diode

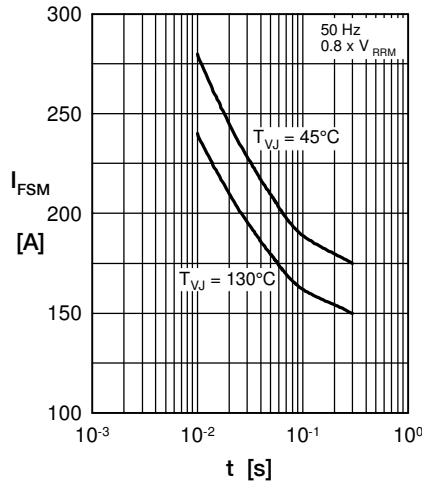


Fig. 2 Surge overload current vs. time per diode

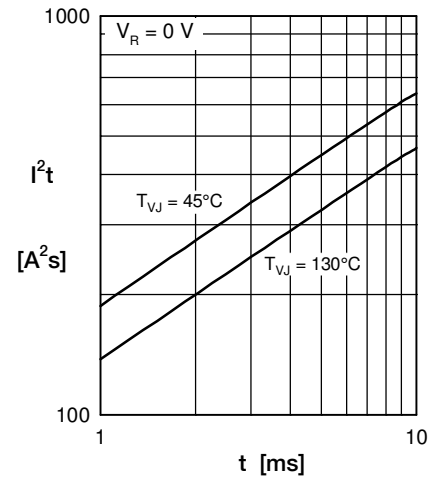


Fig. 3  $I^2t$  vs. time per diode

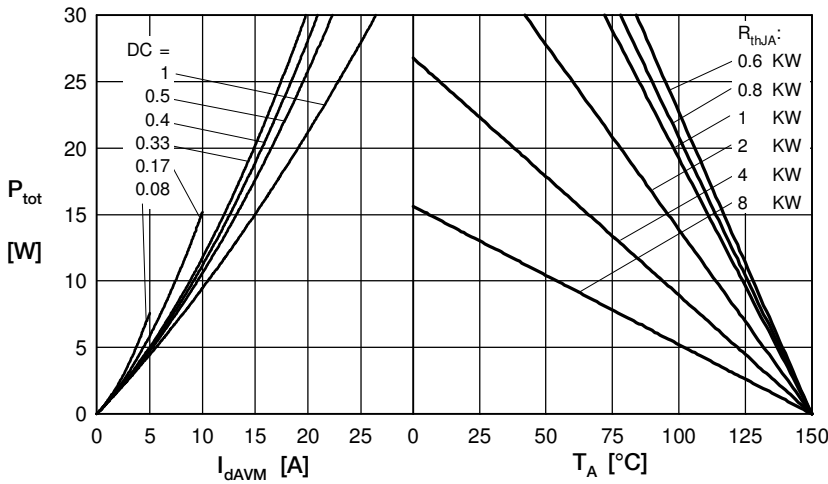


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

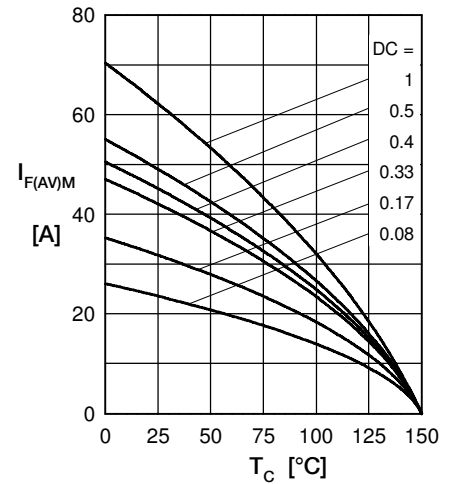


Fig. 5 Max. forward current vs. case temperature per diode

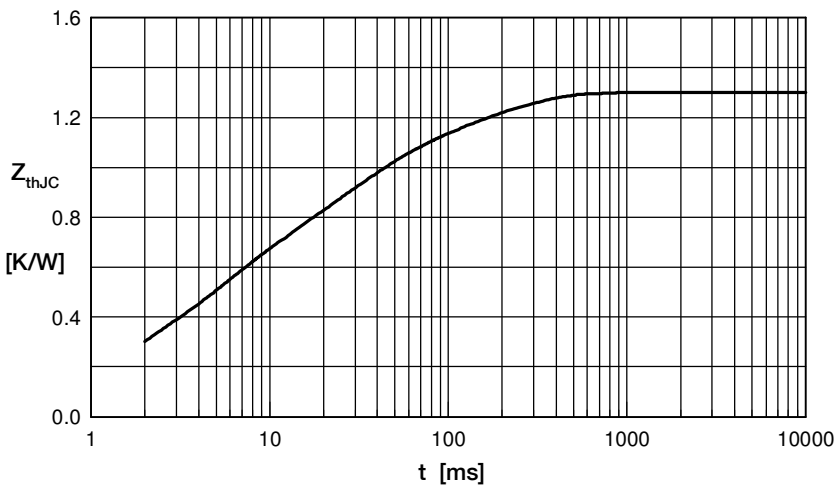


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.06070	0.008
2	0.173	0.05
3	0.3005	0.06
4	0.463	0.3
5	0.3028	0.15